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January 2014

FDMA8051L

Single N-Channel PowerTrench® MOSFET

40 V, 10 A, 14 mΩ

Features

- Max $r_{DS(on)}$ = 14 m Ω at V_{GS} = 10 V, I_D = 10 A
- Max $r_{DS(on)}$ = 18 m Ω at V_{GS} = 4.5 V, I_D = 8.5 A
- Low Profile 0.8 mm maximum in the new package MicroFET 2x2 mm
- Free from halogenated compounds and antimony oxides
- RoHS Compliant

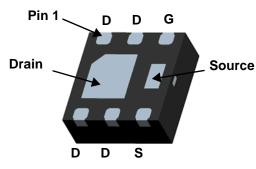
General Description

This device has been designed to provide maximum efficiency and thermal performance for synchronous buck converters. The low rDS(on) and gate charge provide excellent switching performance.

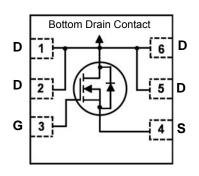
Application

■ DC - DC Buck Converters





MicroFET 2X2 (Bottom View)



MOSFET Maximum Ratings T_A = 25 °C unless otherwise noted

Symbol	Parame		Ratings	Units	
V_{DS}	Drain to Source Voltage		40	V	
V_{GS}	Gate to Source Voltage		±20	V	
	Drain Current -Continuous	T _A = 25 °C	(Note 1a)	10	Δ.
ID	-Pulsed		(Note 3)	80	A
D	Power Dissipation	T _A = 25 °C	(Note 1a)	2.4	W
P_{D}	Power Dissipation $T_A = 25 ^{\circ}\text{C}$ (Note 1b)		(Note 1b)	0.9	VV
T _J , T _{STG}	Operating and Storage Junction Temperature Range			-55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	52	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1b)	145	C/VV

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
051	FDMA8051L	MicroFET 2X2	7 "	8 mm	3000 units

Electrical Characteristics T_J = 25 °C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Chara	cteristics					
BV _{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$	40			V
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	I_D = 250 μ A, referenced to 25 °C		22		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 32 V, V _{GS} = 0 V			1	μΑ
I _{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$			100	nA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	1.0	1.6	3.0	V
$\Delta V_{GS(th)}$ ΔT_J	Gate to Source Threshold Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25 °C		-5		mV/°C
		V _{GS} = 10 V, I _D = 10 A		11	14	
r _{DS(on)}	r _{DS(on)} Static Drain to Source On Resistance	$V_{GS} = 4.5 \text{ V}, I_D = 8.5 \text{ A}$		14	18	mΩ
		V _{GS} = 10 V, I _D = 10 A, T _J = 125 °C		15	19	
9 _{FS}	Forward Transconductance	V _{DD} = 5 V, I _D = 10 A		35		S

Dynamic Characteristics

C _{iss}	Input Capacitance	V - 20 V V - 0 V		901	1260	pF
C _{oss}	Output Capacitance	V _{DS} = 20 V, V _{GS} = 0 V, f = 1 MHz		251	350	pF
C _{rss}	Reverse Transfer Capacitance	1 - 1 101112		16	25	pF
R_g	Gate Resistance		0.1	0.6	1.8	Ω

Switching Characteristics

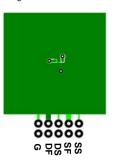
$t_{d(on)}$	Turn-On Delay Time	.,	6.4	13	ns
t _r	Rise Time	$V_{DD} = 20 \text{ V, } I_{D} = 10 \text{ A,}$ $V_{GS} = 10 \text{ V, } R_{GEN} = 6 \Omega$	1.8	10	ns
t _{d(off)}	Turn-Off Delay Time	V _{GS} = 10 V, R _{GEN} = 0 12	17	31	ns
t _f	Fall Time		1.8	10	ns
$Q_{g(TOT)}$	Total Gate Charge	V _{GS} = 0 V to 10 V	14	20	nC
$Q_{g(TOT)}$	Total Gate Charge	$V_{GS} = 0 \text{ V to } 4.5 \text{ V}$ $V_{DD} = 20 \text{ V}$,	6.4	9.0	nC
Q_{gs}	Gate to Source Charge	I _D = 10 A	2.4	3.7	nC
Q_{gd}	Gate to Drain "Miller" Charge		1.8	2.5	nC

Drain-Source Diode Characteristics

1 Von Source to Drain Dioge Forward Voltage	Source to Drain Diode Fenward Voltage	$V_{GS} = 0 V, I_S = 2 A$ (Note 2)	0 V, I _S = 2 A (Note 2) 0.7	0.7	1.2	V
	$V_{GS} = 0 \text{ V}, I_S = 10 \text{ A}$ (Note 2)		8.0	1.2	V	
t _{rr}	Reverse Recovery Time	I _E = 10 A, di/dt = 100 A/μs		23	37	ns
Q _{rr}	Reverse Recovery Charge	- 10 A, α//αι – 100 A/μs		6.7	14	nC

NOTES

^{1.} R_{0,JA} is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. R_{0,JC} is guaranteed by design while R_{0,JA} is determined by the user's board design.



a. 52 °C/W when mounted on a 1 in² pad of 2 oz copper.



b. 145 °C/W when mounted on a minimum pad of 2 oz copper.

^{2.} Pulse Test: Pulse Width < 300 $\mu\text{s},$ Duty cycle < 2.0%.

^{3.} Pulsed Id limited by junction temperature, td<=100 μ S, please refer to SOA curve for more details.

Typical Characteristics T_J = 25°C unless otherwise noted

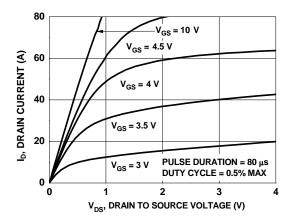


Figure 1. On-Region Characteristics

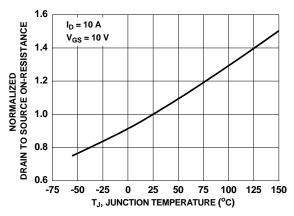


Figure 3. Normalized On-Resistance vs Junction Temperature

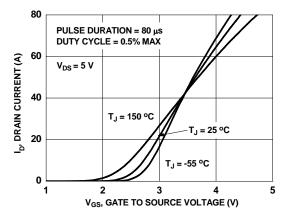


Figure 5. Transfer Characteristics

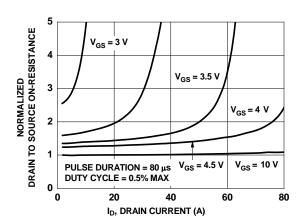


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

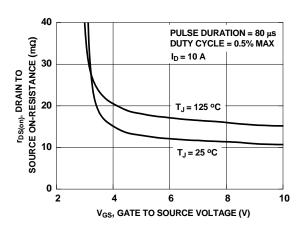


Figure 4. On-Resistance vs Gate to Source Voltage

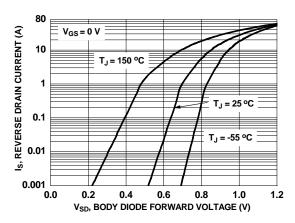


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics $T_J = 25^{\circ}C$ unless otherwise noted

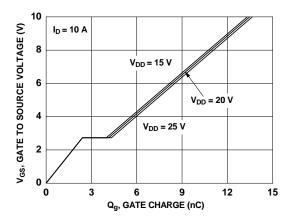


Figure 7. Gate Charge Characteristics

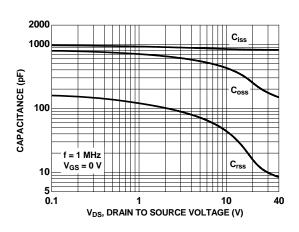
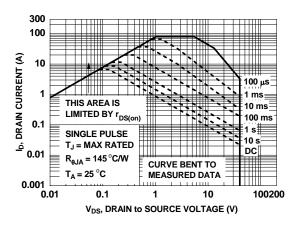


Figure 8. Capacitance vs Drain to Source Voltage



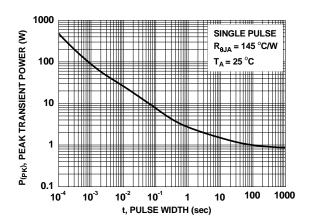


Figure 9. Forward Bias Safe Operating Area

Figure 10. Single Pulse Maximum Power Dissipation

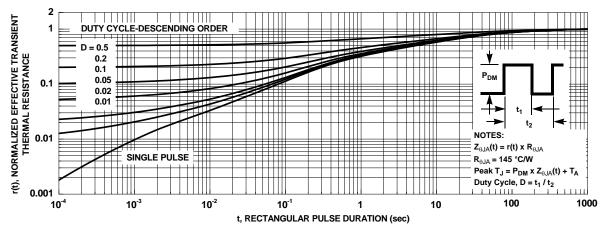
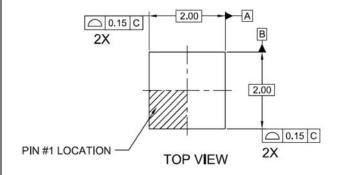
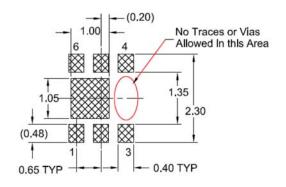


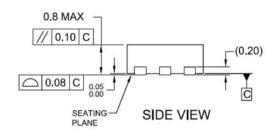
Figure 11. Single Pulse Junction-to-Ambient Transient Thermal Response Curve

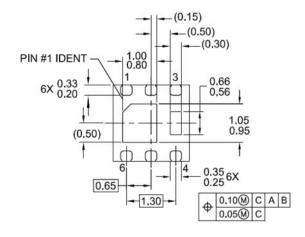
Dimensional Outline and Pad Layout

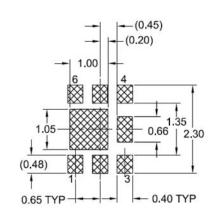




RECOMMENDED LAND PATTERN OPT 1







RECOMMENDED LAND PATTERN OPT 2

NOTES:

A. DOES NOT FULLY CONFORM TO JEDEC REGISTRATION MO-229 DATED AUG/2003

BOTTOM VIEW

- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994
- D. DRAWING FILENAME:





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